CPH3362



http://onsemi.com

Power MOSFET

-100V, 1.7Ω , -0.7A, Single P-Channel

Features

- On-resistance R_{DS}(on)1=1.3 Ω (typ)
- 4V drive

• Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta = 25°C

<u> </u>				
Parameter	Symbol	Conditions	Value	Unit
Drain to Source Voltage	V _{DSS}		-100	>
Gate to Source Voltage	VGSS		±20	>
Drain Current (DC)	ID		-0.7	Α
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-2.8	Α
Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Thermal Resistance Ratings

Parameter	Symbol	Value	Unit
Junction to Ambient	Da	125	°C/W
When mounted on ceramic substrate (900mm ² ×0.8mm)	$R_{\theta JA}$	123	C/VV

Electrical Characteristics at Ta = 25 °C

Description	O. wash ad	Value			11-4	
Parameter	Symbol	Conditions	min	typ	max	Unit V μA μA
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _G S=0V	-100			٧
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-100V, V _{GS} =0V			-1	μА
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μА
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	٧
Forward Transconductance	9FS	V _{DS} =-10V, I _D =-0.3A		1.0		S
	R _{DS} (on)1	I _D =-0.7A, V _G S=-10V		1.3	1.7	Ω
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =-0.3A, V _G S=-4.5V		1.4	1.96	Ω
	R _{DS} (on)3	I _D =-0.3A, V _G S=-4V		1.45	2.1	Ω
Input Capacitance	Ciss			142		pF
Output Capacitance	Coss	V _{DS} =-20V, f=1MHz		12		pF
Reverse Transfer Capacitance	Crss			7.3		pF

Continued on next page.

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

^{*} Machine Model

CPH3362

Continued from preceding page.

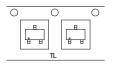
Description	O. was board	Conditions	Value			Linit
Parameter	Symbol	Conditions	min	Тур	max	Unit
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		3.9		ns
Rise Time	t _r			3.4		ns
Turn-OFF Delay Time	t _d (off)			28		ns
Fall Time	tf			12		ns
Total Gate Charge	Qg	V _{DS} =-50V, V _{GS} =-10V, I _D =-0.7A		3.7		nC
Gate to Source Charge	Qgs			0.37		nC
Gate to Drain "Miller" Charge	Qgd			0.86		nC
Forward Diode Voltage	V _{SD}	I _S =-0.7A, V _{GS} =0V		-0.83	-1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Ordering & Package Information

	Device	Package	Shipping	note
Ī	CPH3362-TL-W	CPH3, SC-59 SOT-23, TO-236	3,000 pcs. / reel	Pb-Free and Halogen Free

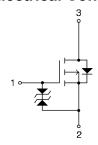
Packing Type:TL



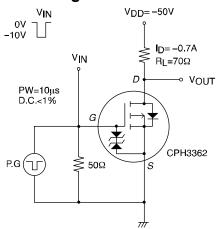
Marking

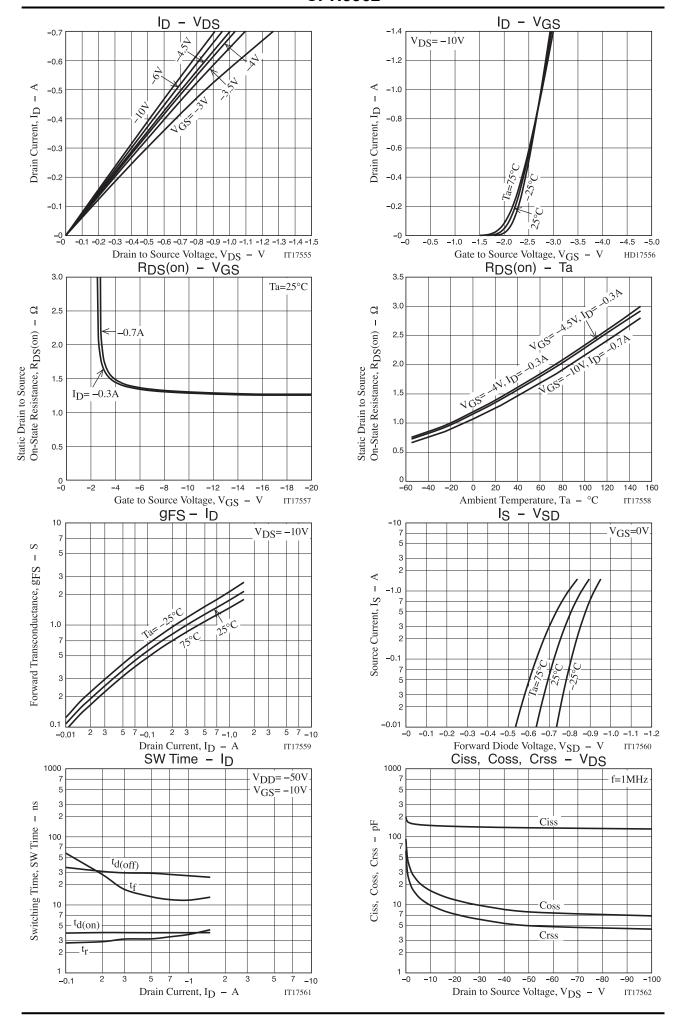


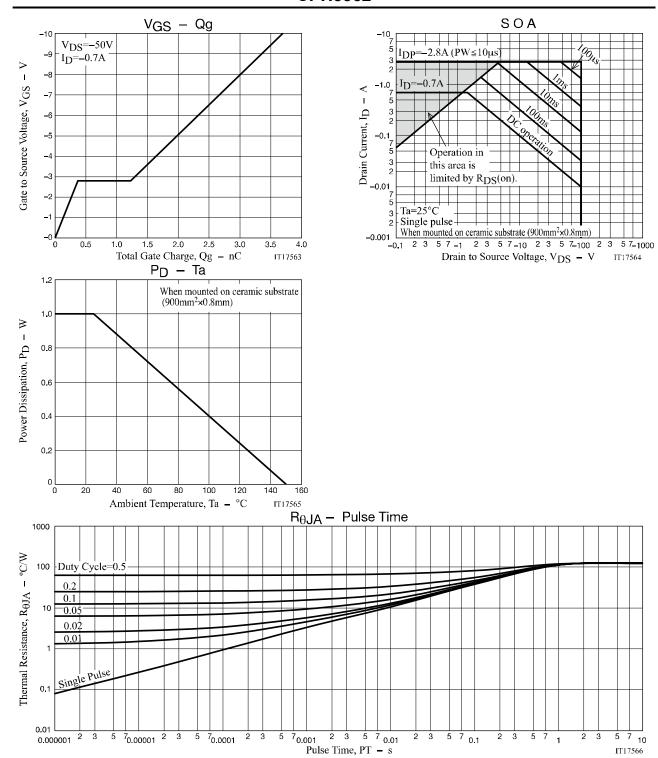
Electrical Connection



Switching Time Test Circuit







Package Dimensions

CPH3362-TL-W

CPH3

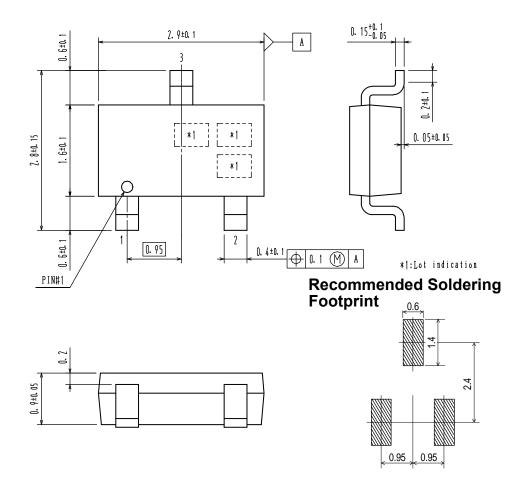
CASE 318BA ISSUE O

unit: mm

1: Gate

2: Source

3: Drain



Note on usage: Since the CPH3362 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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